

a cell plate electrode including a tantalum nitride film formed on and contacting an upper surface of said tantalum oxide film and a copper film formed on and contacting an upper surface of said tantalum nitride film.

3. (Amended) A semiconductor device, comprising:

a semiconductor substrate;

a contact plug including tungsten formed on the semiconductor substrate;

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a storage electrode including a first indium oxide film formed on and contacting an upper surface of said contact plug ;

a capacitor dielectric film including a tantalum oxide film formed on and contacting an upper surface of said first indium oxide film; and

a cell plate electrode including a second indium oxide film formed on and contacting an upper surface of said tantalum oxide film.

4. (Amended) The semiconductor device according to claim 3, wherein said storage electrode further includes a tantalum nitride film formed beneath and contacting a lower surface of said first indium oxide film.

5. (Amended) The semiconductor device according to claim 3, wherein said cell plate electrode further includes a copper film formed on said second indium oxide film.